

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON) \max}$	Package	I_D $T_A = +25^\circ\text{C}$
-20V	0.9Ω @ $V_{GS} = -4.5\text{V}$	SOT23	-430mA
	2.0Ω @ $V_{GS} = -1.8\text{V}$		-150mA

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions

Features

- Low On-Resistance
- Very Low Gate Threshold Voltage $V_{GS(TH)} < 1\text{V}$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- ESD Protected Gate
- Qualified to AEC-Q101 standards for High Reliability

Mechanical Data

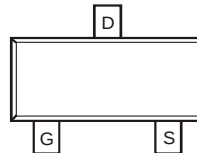
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding
- Compound: UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin annealed over Copper leadframe.
- Solderable per MIL-STD-202, Method 208 **(e3)**
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



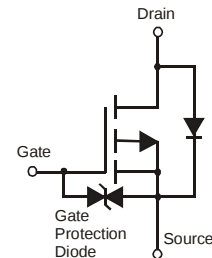
SOT23



Top View



Top View
Internal Schematic



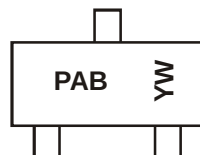
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
DMP2004K-7	Commercial	SOT23	3,000/Tape & Reel
DMP2004KQ-7	Automotive	SOT23	3,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 - See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



PAB = Product Type Marking Code
 YW = Date Code Marking
 Y = Year (ex: W = 2009)
 W = Week (ex: A ~ Z = Weeks 1 ~ 26
 a ~ y = Weeks 27 ~ 51
 z = Weeks 52 and 53)

Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015
Code	V	W	X	Y	Z	A	B	C

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±8	V
Continuous Drain Current (Note 5) V _{GS} = -4.5V	I _D	-600	mA
Pulsed Drain Current	I _{DM}	-1.9	A

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	550	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	227	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±1.0	μA	V _{GS} = ±4.5V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	-0.5	—	-1.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	0.7	0.9	Ω	V _{GS} = -4.5V, I _D = -430mA
		—	1.1	1.4		V _{GS} = -2.5V, I _D = -300mA
		—	1.7	2.0		V _{GS} = -1.8V, I _D = -150mA
		—	—	—		V _{GS} = -1.8V, I _D = -150mA
Forward Transfer Admittance	Y _{fs}	200	—	—	mS	V _{DS} = -10V, I _D = -0.2A
Diode Forward Voltage (Note 6)	V _{SD}	-0.5	—	-1.2	V	V _{GS} = 0V, I _S = -115mA
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	—	—	175	pF	V _{DS} = -16V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	—	30	pF	
Reverse Transfer Capacitance	C _{rss}	—	—	20	pF	
Turn-On Delay Time	t _{D(on)}	—	8.5	—	ns	V _{DD} = -3V, V _{GS} = -2.5V, R _L = 300Ω, R _G = 25Ω, I _D = -100mA
Turn-On Rise Time	t _r	—	4.3	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	20.2	—	ns	
Turn-Off Fall Time	t _f	—	19.2	—	ns	

Notes: 5. Device mounted on FR-4 PCB.
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

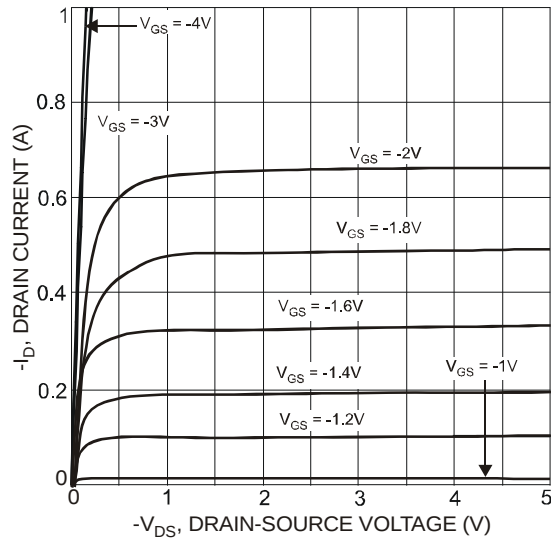


Figure 1 Typical Output Characteristics

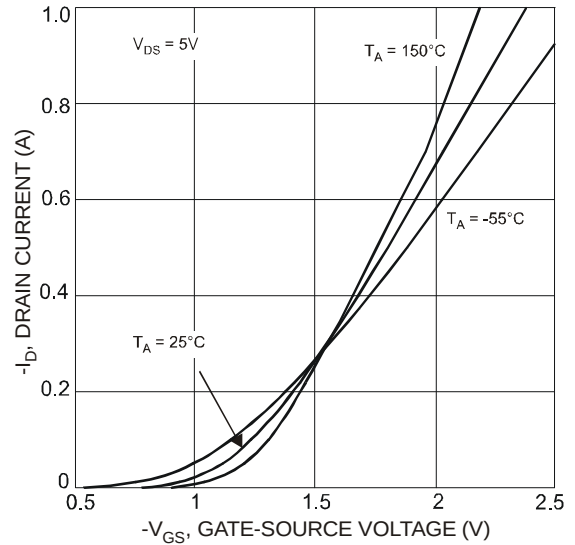


Figure 2 Typical Transfer Characteristics

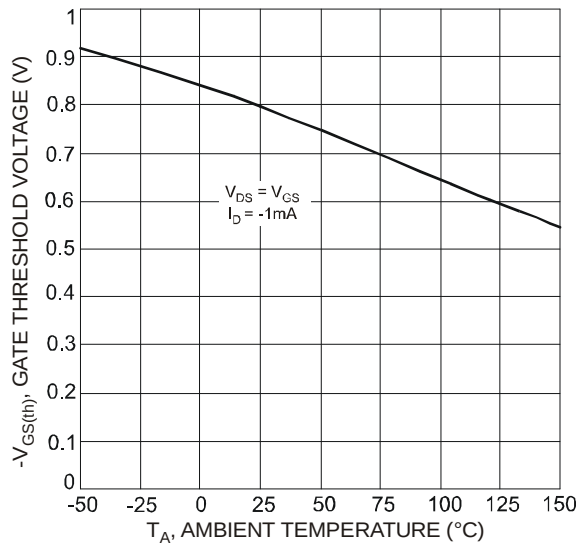


Figure 3 Gate Threshold Voltage vs. Ambient Temperature

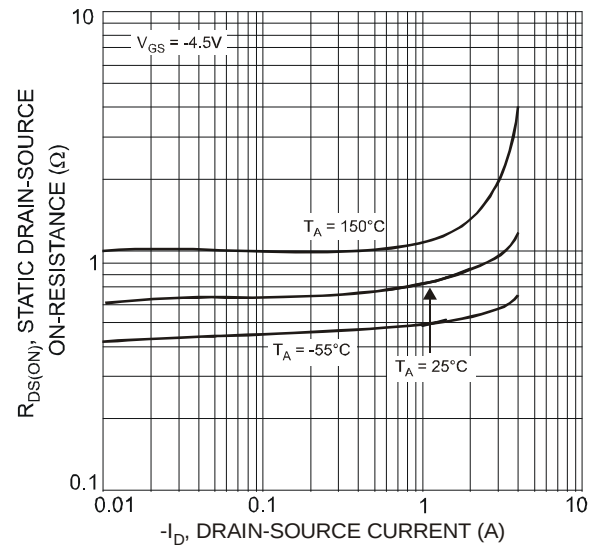


Figure 4 Static Drain-Source On-Resistance vs. Drain Current

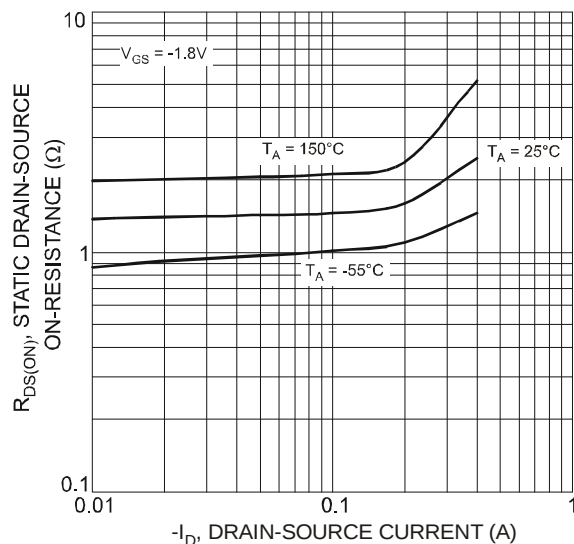


Figure 5 Static Drain-Source On-Resistance vs. Drain Current

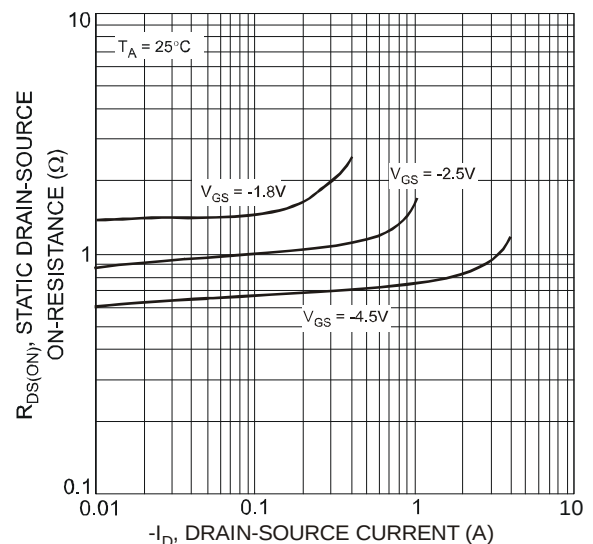


Figure 6 Static Drain-Source On-Resistance vs. Drain-Source Current

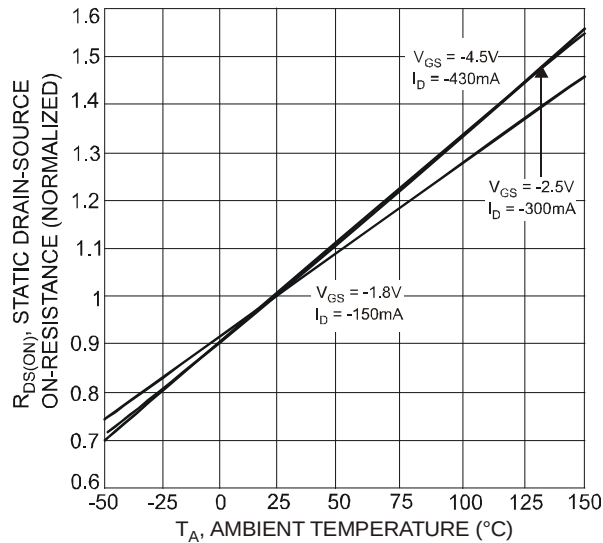


Figure 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

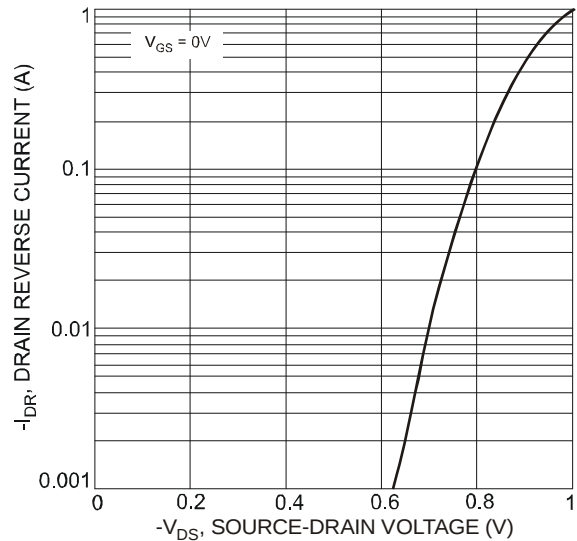


Figure 8 Reverse Drain Current vs. Source-Drain Voltage

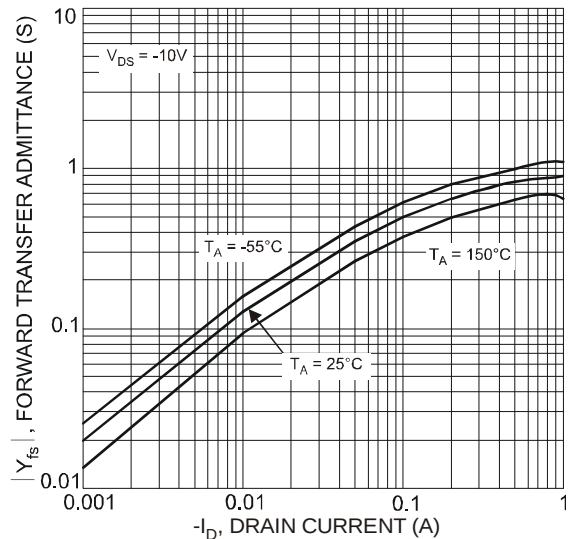


Figure 9 Forward Transfer Admittance vs. Drain Current

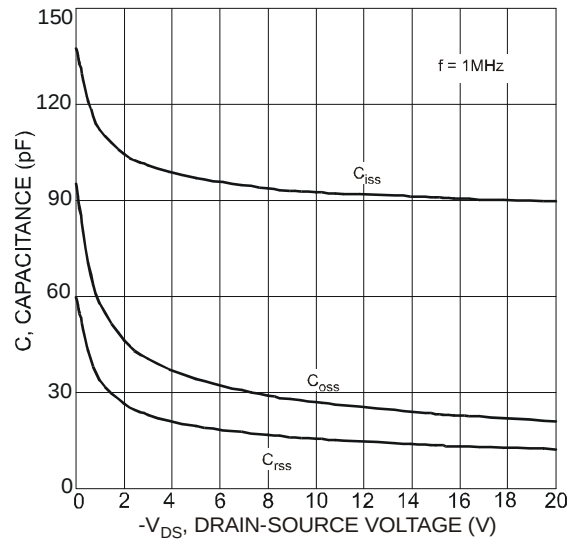
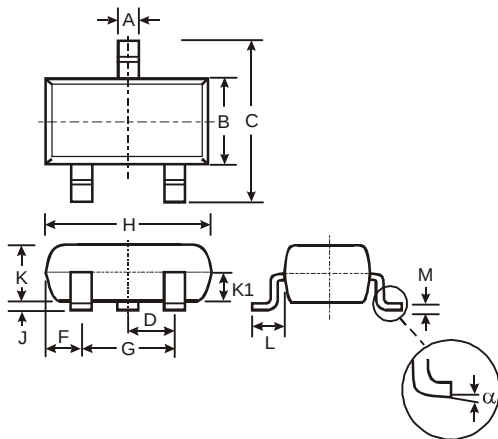


Figure 10 Typical Capacitance

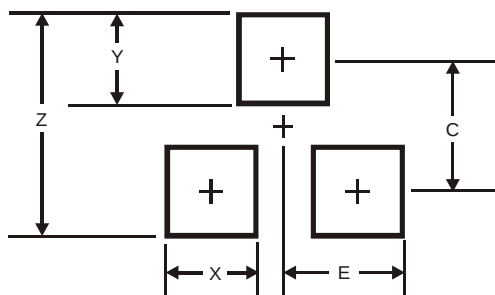
Package Outline Dimensions



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-

All Dimensions in mm

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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